

ABSTRACT

Embodiments of the present application provide a semiconductor structure treatment method and a semiconductor structure forming method. The semiconductor structure treatment method comprises: providing a semiconductor substrate (111), feature portions (112) being provided on the semiconductor substrate (111), and mask layers (200) being provided on the tops of the feature portions (112); performing ashing treatment on the semiconductor structure, the semiconductor structure comprising the semiconductor substrate (111), the feature portions (112) and the mask layers (200); removing the mask layers (200); performing washing treatment on the semiconductor structure, oxide layers (120) being formed on surfaces of the feature portions (112) after performing the washing treatment on the feature portions (112); performing drying treatment on the semiconductor structure; and removing the oxide layers (120). During the drying treatment, one feature portion in at least one group of adjacent feature portions (112) is inclined towards the adjacent feature portion (112), moreover, the distance between the inclined feature portion (112) and the adjacent feature portion (112) after the drying treatment is smaller than the distance therebetween before the drying treatment.

FIG. 6